

**TO-92 Bipolar Transistor 双极型三极管**

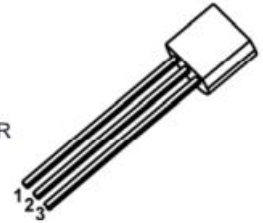
■ **Features 特点**

**PNP General Purpose 通用**

■ **Absolute Maximum Ratings 最大额定值**

**TO - 92**

1.EMITTER  
2.COLLECTOR  
3.BASE



Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	$V_{CBO}$	-35	V
Collector-Emitter Voltage 集电极发射极电压	$V_{CEO}$	-30	V
Emitter-Base Voltage 发射极基极电压	$V_{EBO}$	-5	V
Collector Current 集电极电流	$I_C$	-800	mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ\text{C})$	625	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	-55to+150 $^\circ\text{C}$	

■ **Device Marking 产品打标**

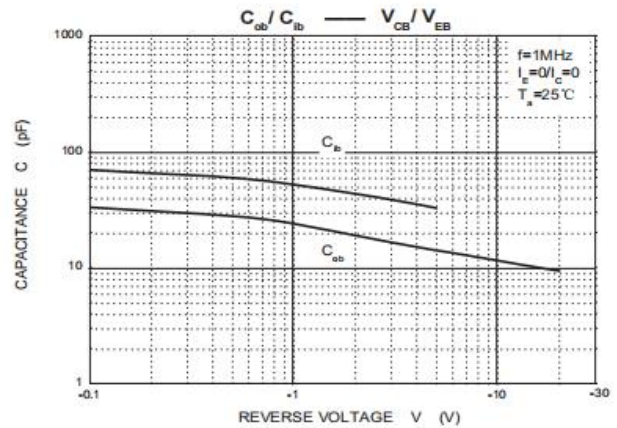
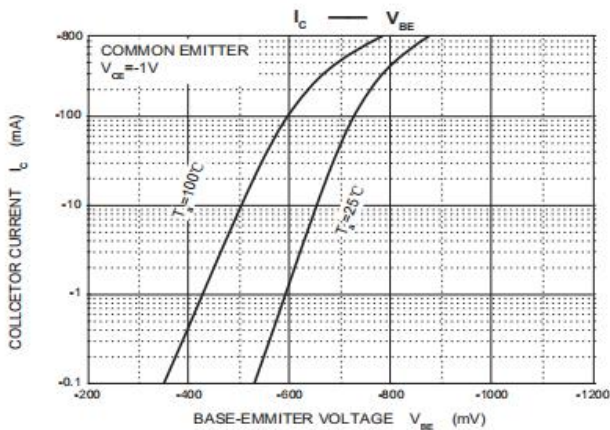
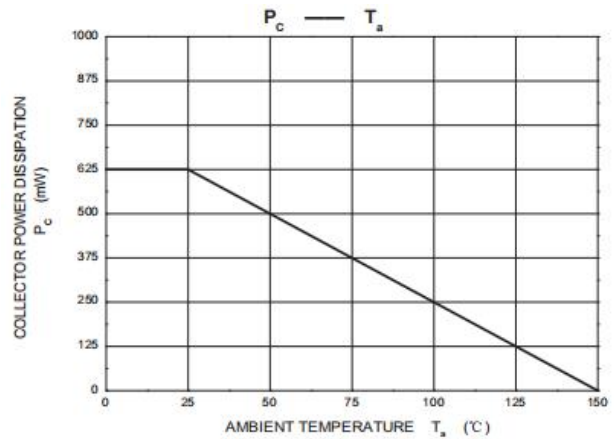
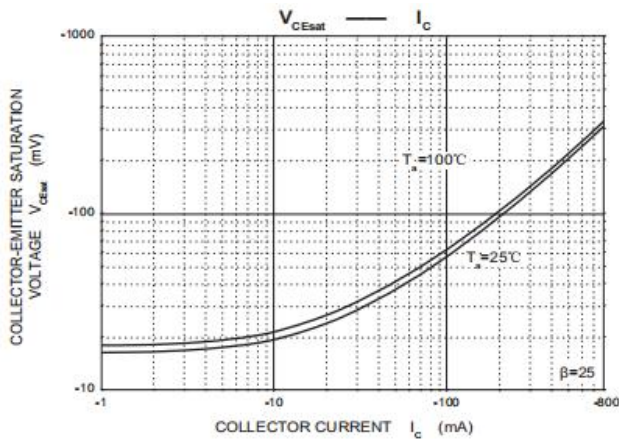
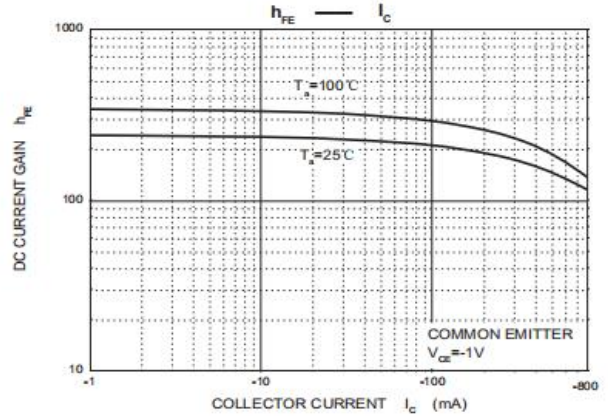
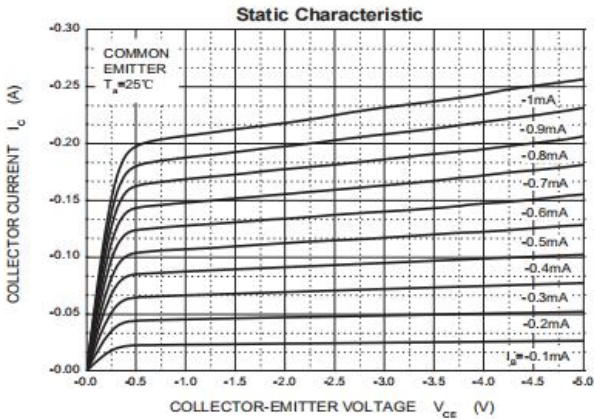
$H_{FE}(1)$	100-200(O)	160-320(Y)
Mark	A1271	

■ Electrical Characteristics 电特性

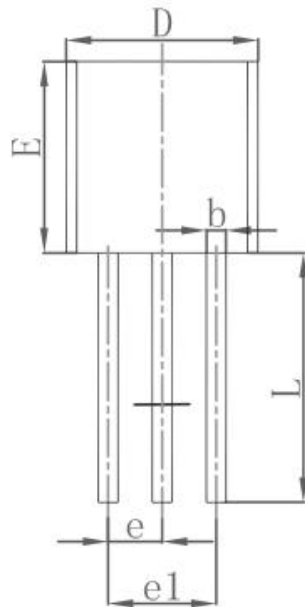
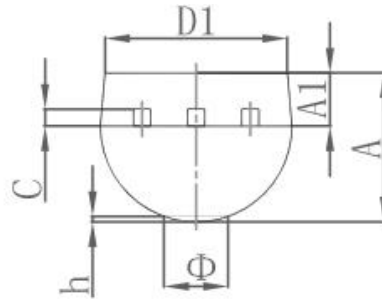
( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压( $I_C=-100\mu\text{A}$ , $I_E=0$ )	$BV_{CBO}$	-35	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压( $I_C=-10\text{mA}$ , $I_B=0$ )	$BV_{CEO}$	-30	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压( $I_E=-100\mu\text{A}$ , $I_C=0$ )	$BV_{EBO}$	-5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流( $V_{CB}=-35\text{V}$ , $I_E=0$ )	$I_{CBO}$	—	—	-0.1	$\mu\text{A}$
Collector-Emitter Leakage Current 集电极发射漏电流( $V_{CE}=-25\text{V}$ , $I_E=0$ )	$I_{CBO}$	—	—	-0.2	$\mu\text{A}$
Emitter-Base Leakage Current 发射极基极漏电流( $V_{EB}=-5\text{V}$ , $I_C=0$ )	$I_{EBO}$	—	—	-0.1	$\mu\text{A}$
DC Current Gain 直流电流增益( $V_{CE}=-1\text{V}$ , $I_C=-100\text{mA}$ )	$H_{FE(1)}$	100	—	320	
DC Current Gain 直流电流增益( $V_{CE}=-1\text{V}$ , $I_C=-700\text{mA}$ )	$H_{FE(2)}$	35	—	—	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降( $I_C=-500\text{mA}$ , $I_B=-20\text{mA}$ )	$V_{CE(sat)}$	—	—	-0.7	V
Base-Emitter On Voltage 基极发射极导通电压( $V_{CE}=-1\text{V}$ , $I_C=-10\text{mA}$ )	$V_{BE(on)}$	—	—	-0.8	V
Output Capacitance 输出电容( $V_{CB}=-10\text{V}$ , $I_E=0$ , $f=1\text{MHz}$ )	$C_{ob}$	—	19	—	pF
Transition Frequency 特征频率( $V_{CE}=-5\text{V}$ , $I_C=-10\text{mA}$ )	$f_T$	—	120	—	MHz

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015